

/ Descriptions

TO-252 N MOS N-CHANNEL MOSFET in a TO-252 Plastic Package.

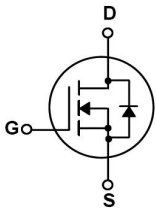
/ Features

Low gate charge, low crss, fast switching.

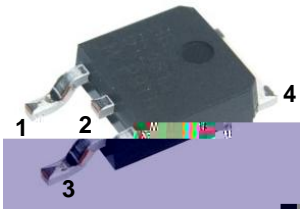
/ Applications

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S PIN 4 D

/ h_{FE} Classifications & Marking

See Marking Instructions.

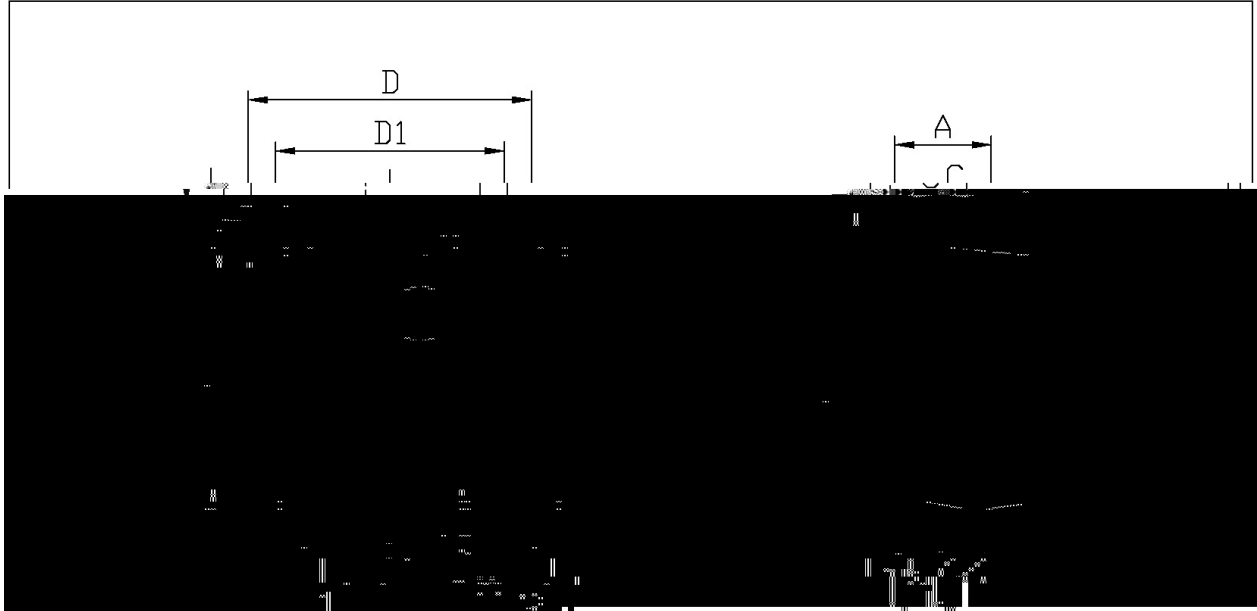
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	5.0	A
Drain Current	$I_D(T_C=100^\circ\text{C})$	2.6	A
Drain Current - Pulsed	I_{DM}	18	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	210	mJ
Repetitive Avalanche Energy	E_{AR}	10	mJ
Avalanche Current	I_{AR}	4.5	A
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	54	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V$ $V_{GS}=0V$			1.0	μA
		$V_{DS}=480V$ $T_C=125^\circ\text{C}$			10	μA
Gate-Body Leakage Current, Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=2.25A$		2.0	2.5	
Forward Transconductance	g_{FS}	$V_{DS}=40V$ $I_D=2.25A$		4.7		S

$V_{GS}=0V$ $I_D=2.25A$ $T_C=25^\circ\text{C}$ $V_{DS}=40V$ $I_D=2.25A$ $T_C=25^\circ\text{C}$ $V_{GS}=10V$ $I_D=2.25A$ $T_C=25^\circ\text{C}$ $V_{GS}=\pm 30V$ $V_{DS}=0V$ $T_C=25^\circ\text{C}$ $V_{DS}=650V$ $V_{GS}=0V$ $T_C=25^\circ\text{C}$ $V_{DS}=480V$ $T_C=125^\circ\text{C}$ $V_{GS}=0V$ $I_D=250\mu A$ $T_C=25^\circ\text{C}$

BRD5N65
Rev.A Sep.-2016

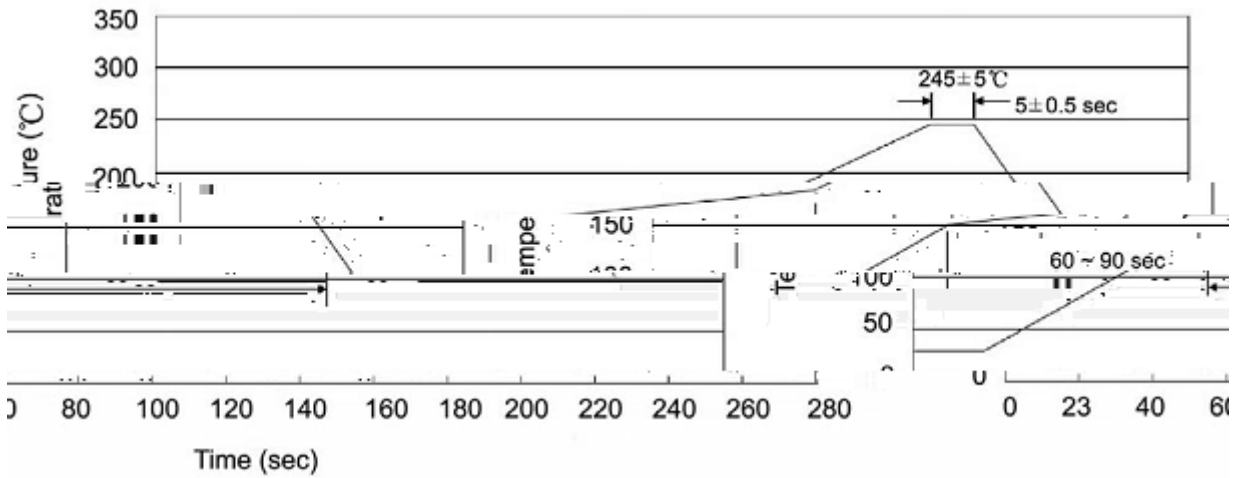
/ Package Dimensions



Symbol	Parameter	Unit	Min	Max
D	Package Width	mm	10.0	10.0
D1	Package Width (Central)	mm	6.0	6.0
A	Package Width (Right)	mm	2.0	2.0
C	Package Width (Right)	mm	2.0	2.0
H	Package Height	mm	0.5	0.5
L	Lead Length	mm	0.5	0.5
S	Lead Spacing	mm	0.5	0.5
T	Lead Thickness	mm	0.1	0.1
W	Lead Width	mm	0.2	0.2
P	Pitch	mm	0.5	0.5
E	Lead Extension	mm	0.5	0.5
F	Lead Form	mm	0.5	0.5
G	Lead Angle	deg	0	0
R	Lead Radius	mm	0.1	0.1
U	Lead Undercut	mm	0.1	0.1
V	Lead Voltage	V	0	0
W	Lead Weight	g	0	0
X	Lead X-axis	mm	0	0
Y	Lead Y-axis	mm	0	0
Z	Lead Z-axis	mm	0	0



() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|--------|-----|------------|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245..5 | | 5..0.5sec; | | 2.Peak Temp.:245..5 , Duration:5..0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260..5 10..1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量		Dimension 包装尺寸 (unit: mm ³)
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒